Supplementary information

Nanostructuring few-layer graphene films by swift heavy ions for electronic application: tuning of electronic and transport properties


Fig. S1. Histograms of distributions of pores on size and distances between pores extracted from SEM images for samples irradiated with ion fluence of $3 \times 10^{11}$ cm$^{-2}$ and different energies. Comparison of the histograms demonstrates that parameters of pores for energies 26 and 46 MeV are very similar. The size of pores created by ions with energy 77 and 167 MeV and the distance between them are also closed one to another and slightly higher than that of the previous group of samples.

Fig. S2. Histograms of distributions of pores on size extracted from AFM images for samples irradiated with ion fluence of $3 \times 10^{11}$ cm$^{-2}$ and energies 26 and 167 MeV. Determination of the distance between pores in the case of AFM was hampered by large noises on the surface relief and ambiguity in the determination of this distance. This feature also can give higher values of pore size.
than that extracted from SEM data. Difference between the size of pores in samples irradiated with 26 MeV and 167 MeV ions is looked more pronounced.

Fig. S3. (a) Dependence of the current $I_{ds}$ on the gate voltage $V_g$ at $U_{DS} = 0.2$ V for FLG film (thickness ~2 nm) irradiated with 77-MeV ions to a dose of $3 \times 10^{11}$ ion/cm$^2$. Two curves correspond to repeated measurements. Carrier mobility calculated from few repeated measurements are equal to $\mu_h = 630-830$ cm$^2$/Vs and $\mu_e = 630-830$ cm$^2$/Vs. (b) Dependence of the current $I_{ds}$ on the gate voltage $V_g$ at $U_{DS} = 0.2$ V for FLG film (thickness ~2.5 nm) irradiated with 167-MeV ions to a dose of $1 \times 10^{11}$ ion/cm$^2$. Carrier mobility calculated from few repeated measurements are equal to $\mu_h = 100-120$ cm$^2$/Vs and $\mu_e = 980-1350$ cm$^2$/Vs.